E Nanotech Semiconductor

Short-Form Datasheet NT22030

Low Cost 3.3 V Transmitter IC for LED based Fast Ethernet applications over Optical Fiber

Main Features

- Up to 25 mA modulation current
- Fabricated in standard high-volume, low cost, 'digital' CMOS process
- Compatible with the latest Fast Ethernet specification
- Less than 14.75 mA total current consumption (excluding drive current)
- Differential LVDS input with AC-coupled CML compatibility
- Supports LED with mask-programmed onchip Temperature Compensation and Pulse Width Adjust
- 3.3 V supply
- High temperature operation (up to 125 °C junction temperature)
- No external components within FOT required

Application

Fast Ethernet

General Description

The NT22030 is a full-custom CMOS IC designed for high-speed LED drive for applications such as Fast Ethernet over POF.

The drive current can be set by an external resistor (defined as two 15 k Ω resistors in parallel) using the I_{MODSET} pad or using an onchip resistor by connecting I_{MODSET} to GND. 3 dB optical power reduction functionality is also supported by connecting this pad to VCC.

The NT22030 driver IC will be supplied in die form, with a clearly visible orientation.

For full datasheet, pricing, ordering and delivery information, please e-mail Nanotech Semiconductor at <u>sales@nanosemi.co.uk</u> or visit our website at <u>www.nanosemi.co.uk</u>.



Short-Form Datasheet NT22030

Chip Padout



Figure 1 - Bare die – 990 µm x 810 µm plus 80 µm scribe lane 150 µm pad pitch, 96 µm pads (86 µm passivation opening)

Pad Descriptions

Pad No.	Name	Function
1	DINB	LVDS Complimentary Data Input. Also supports AC-coupled CML.
2	DIN	LVDS Data Input. High for maximum emitter illumination. Also supports AC-coupled CML.
3	SLPEN	Sleep padTake to GND for normal operation to disable sleep mode. Floating to enable sleep mode.
4	VCC	Power pad. Connect to most positive supply.
5	VCC	Power pad. Connect to most positive supply.
6	IMODSET	Multifunction control pin: Bonded to GND – internal preset modulation current, Resistor to GND [2 [*] 15 k Ω in parallel] – programmable modulation current, Bonded to V _{cc} – internal preset current / 2 (3 dB reduction)
7	ILED	Driver output. Connect LED cathode to this pad. Sinks current when DIN is taken high, holds a predetermined voltage wrt $V_{\rm CC}$ when DIN is taken low.
8	GND	Ground pad. Connect to the most negative supply.
9	GND	Ground pad. Connect to the most negative supply.
10	IMON	Current source equal to LED drive current / 25. Used to measure actual drive current through LED during FOT test using resistor to GND. For Boost bond to GND – this enables a 20 % increase in drive current